2816A/5516A
Timer E^2
16K Electrically Erasable PROMs

October 1988

Features

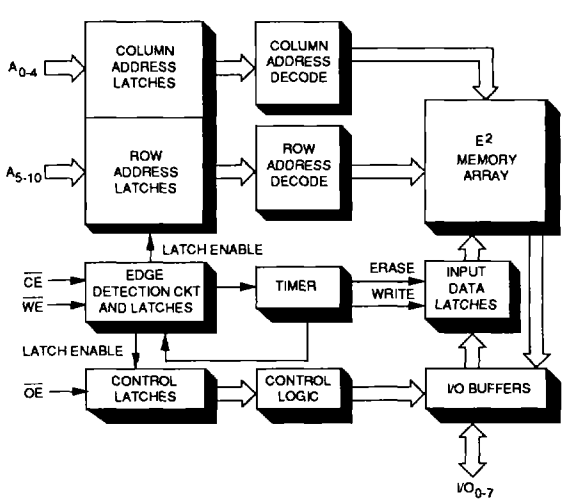
- **High Endurance Write Cycles**
  - **5516A : 1,000,000 Cycles/Byte Minimum**
  - **2816A: 10,000 Cycles/Byte Minimum**
- **On-Chip Timer**
  - **Automatic Erase and Write Time Out**
  - **2 ms Byte Write Time (2816AH)**
- **All Inputs Latched by Write or Chip Enable**
- **5 V ± 10% Power Supply**
- **Power Up/Down Protection Circuitry**
- **200 ns max. Access Time**
- **Low Power Operation**
  - **110 mA max. Active Current**
  - **40 mA max. Standby Current**
- **JEDEC Approved Byte-Wide Pinout**
- **Military and Extended Temperature Range Available**

Description

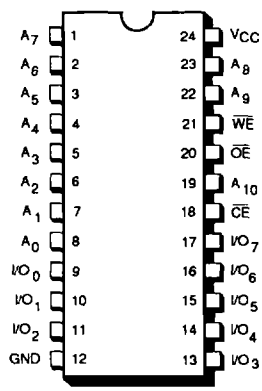
SEEQ's 5516A and 2816A are 5V only, 2Kx8 electrically erasable programmable read only memories (EEPROMs). EEPROMs are ideal for applications which require non-volatility and in-system data modification. The endurance, the minimum number of times that a byte may be written, is ***1 million*** *for the 5516A and 10 thousand for the 2816A. The 5516A's extraordinary high endurance was accomplished using SEEQ's proprietary oxyntride EEPROM process and its innovative Q Cell™ design. The 5516A is ideal for systems that require frequent updates.*

Both EEPROMs have an internal timer that automatically times out the write time. A separate erase cycle is not required and the minimum write enable ($\overline{WE}$) pulse width needs to be only 150 ns. The on-chip timer, along with the inputs being latched by a write or chip enable signal edge, frees the microcomputer system for other tasks during the write time. The standard 2816A and 5516A's write time is 10 ms, while the 2816AH's write time is a fast 2 ms. Once

Block Diagram



Pin Configuration



Pin Names

A_0-A_{10}	ADDRESSES
$\overline{CE}$	CHIP ENABLE
$\overline{OE}$	OUTPUT ENABLE
$\overline{WE}$	WRITE ENABLE
I/O_{0-7}	DATA INPUT (WRITE OR ERASE) DATA OUTPUT (READ)

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a byte is written, it can be read in 200 ns. The inputs are TTL for both the byte write and read mode.

Device Operation

There are five operational modes (see Table 1) and, except for the chip erase mode [2], only TTL inputs are required. To write into a particular location, a TTL low is applied to the write enable ($\overline{WE}$) pin of a selected ($\overline{CE}$ low) device. This, combined with output enable ($\overline{OE}$) being high, initiates a write cycle. During a byte write cycle, addresses are latched on the last falling edge of $\overline{CE}$ or $\overline{WE}$ and data is latched on the first rising edge of $\overline{CE}$ or $\overline{WE}$. An internal timer times out the required byte write time. An automatic byte erase is performed internally in the byte write mode.

Absolute Maximum Stress Ratings*

Temperature
Storage ..... −65° C to +150° C
Under Bias ..... −10° C to +80° C
D.C. Voltage applied to all Inputs or Outputs with respect to ground ..... +6.0 V to −0.5 V
Undershoot/Overshoot pulse of less then 10 ns (measured at 50% point) applied to all inputs or outputs with respect to ground .... (undershoot) −1.0 V (overshoot) + 7.0 V

Mode Selection (Table 1)

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O
Read	V_{IL}	V_{IL}	V_{IH}	D_{OUT}
Standby	V_{IH}	X	X	High Z
Byte Write	V_{IL}	V_{IH}	V_{IL}	D_{IN}
Write	X	V_{IL}	X	High Z/D_{OUT}
Inhibit	X	X	V_{IH}	High Z/D_{OUT}

X: any TTL level

Power Up/Down Considerations

The 2816A/5516A has internal circuitry to minimize a false write during system V_{CC} power up or down. This circuitry prevents writing under any one of the following conditions.

1. *V_{CC} is less than 3V.[3]*
2. *A negative Write Enable ($\overline{WE}$) transition has not occured when V_{CC} is between 3 V and 5 V.*

Writing will also be prevented if $\overline{CE}$ or $\overline{OE}$ are in a logical state other than that specified for a byte write in the Mode Selection table.

"COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

	5516A/5516AH 2816A/2816AH
Temperature Range (Ambient)	0°C to 70°C
V_{CC} Supply Voltage	5V ± 10%

Endurance and Data Retention

Symbol	Parameter	Value	Units	Condition
N	Minimum Endurance	10,000 1,000,000[1]	Cycles/Byte	MIL-STD 883 Test Method 1033
T_{DR}	Data Retention	>10	Years	MIL-STD 883 Test Method 1008

NOTES:
1. 5516A-1 million cycles/byte.
2. Chip Erase is an optional mode.
3. Characterized. Not tested.

DC Operating Characteristics T_A = 0° to 70°C, V_{CC} = 5 V ± 10% unless otherwise noted

Symbol	Parameter	Limits Min.	Limits Max.	Units	Test Condition
I_{CC}	Active V_{CC} Current		110	mA	$\overline{CE}$ = $\overline{OE}$ = V_{IL}; All I/O Open; Other Inputs = 5.5 V
I_{SB}	Standby V_{CC} Current		40	mA	$\overline{CE}$ = V_{IH}, $\overline{OE}$ = V_{IL}; All I/O's Open; Other Inputs = 5.5 V
I_{LI}	Input Leakage Current		10	µA	V_{IN} = 5.5 V
I_{LO}	Output Leakage Current		10	µA	V_{OUT} = 5.5 V
V_{IL}	Input Low Voltage	–0.1	0.8	V	
V_{IH}	Input High Voltage	2.0	6	V	
V_{OL}	Output Low Voltage		0.4	V	I_{OL} = 2.1 mA
V_{OH}	Output High Voltage	2.4		V	I_{OH} = –400 µA

AC Characteristics

Read Operation T_A=0° to 70° C, V_{CC}=5 V ± 10% unless otherwise noted

Symbol	Parameter	5516A/5516AH-200 / 2816A/2816AH-200 Min.	5516A/5516AH-200 / 2816A/2816AH-200 Max.	5516A/5516AH-250 / 2816A/2816AH-250 Min.	5516A/5516AH-250 / 2816A/2816AH-250 Max.	5516A/5516AH-300 / 2816A/2816AH-300 Min.	5516A/5516AH-300 / 2816A/2816AH-300 Max.	2816A-350 Min.	2816A-350 Max.	Units
t_{RC}	Read Cycle Time	200		250		300		350		ns
t_{CE}	Chip Enable Access Time		200		250		300		350	ns
t_{AA}	Address Access Time		200		250		300		350	ns
t_{OE}	Output Enable Access Time		90		90		100		100	ns
t_{LZ}	$\overline{CE}$ to Output in Low Z	10		10		10		10		ns
t_{HZ}	$\overline{CE}$ to Output in High Z		100		100		100		100	ns
t_{OLZ}	$\overline{OE}$ to Output in Low Z	50		50		50		50		ns
t_{OHZ}	$\overline{OE}$ to Output in High Z		100		100		100		100	ns
t_{OH}[1]	Output Hold from Addr Change	20		20		20		20		ns
t_{PU}[1]	$\overline{CE}$ to Power-up Time	0		0		0		0		ns
t_{PD}[1]	$\overline{CE}$ to Power Down Time		50		50		50		50	ns

Capacitance [2] T_A = 25°C, f = 1 MHz

Symbol	Parameter	Max Conditions
C_{IN}	Input Capacitance	6 pF V_{IN} = 0 V
C_{OUT}	Data (I/O) Capacitance	10 pF $V_{I/O}$ = 0 V

E.S.D. Characteristics

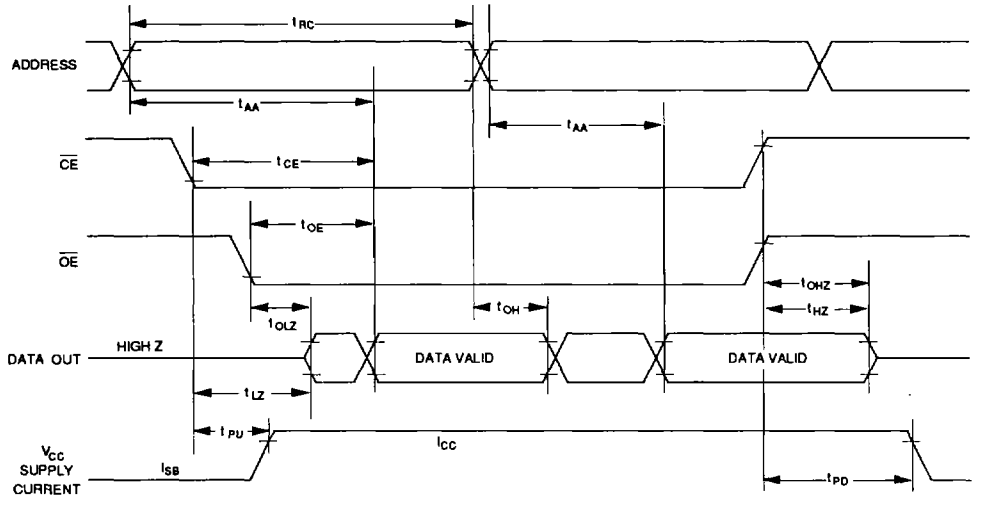
Symbol	Parameter	Value	Test Conditions
V_{ZAP}[1]	E.S.D. Tolerance	>2000 V	MIL-STD 883 Test Method 3015

A.C. Test Conditions

Output Load: 1 TTL gate and C_L = 100 pF
Input Rise and Fall Times: < 20 ns
Input Pulse Levels: 0.45 V to 2.4 V
Timing Measurement Reference Level:
Inputs 1 V and 2 V
Outputs 0.8 V and 2 V

NOTES:
1. Characterized. Not tested.
2. *This parameter measured only for the initial qualification and after process or design changes which may affect capacitance.*

Read Cycle Timing



AC Characteristics

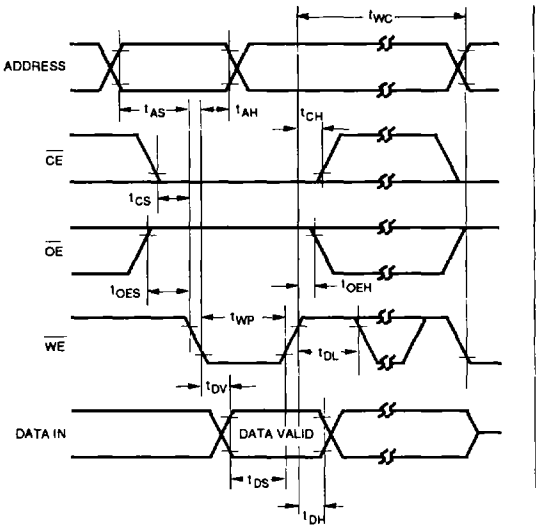
Write Operation T_A=0° to 70°C, V_{CC}=5 V ± 10% unless otherwise noted

Symbol	Parameter	Limits								Units
		5516A-200 2816A/2816AH-200		5516A-250 2816A/2816AH-250		5516A-300 2816A/2816AH-300		2816A-350		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{WC}	Write Cycle Time 5516AH/2816AH		2		2		2	—	—	ms
	5516A/2816A		10		10		10		10	ms
t_{AS}	Address Set Up Time	10		10		10		10		ns
t_{AH}	Address Hold Time	50		50		70		70		ns
t_{CS}	Write Set Up Time	0		0		0		0		ns
t_{CH}	Write Hold Time	0		0		0		0		ns
t_{CW}	$\overline{CE}$ to End of Write Input	150		150		150		150		ns
t_{OES}	$\overline{OE}$ Set Up Time	10		10		10		10		ns
t_{OEH}	$\overline{OE}$ Hold Time	10		10		10		10		ns
t_{WP}[1]	$\overline{WE}$ Write Pulse Width	150		150		150		150		ns
t_{DL}	Data Latch Time	50		50		50		50		ns
t_{DV}[2]	Data Valid Time		1		1		1		1	µs
t_{DS}	Data Set Up Time	50		50		50		50		ns
t_{DH}	Data Hold Time	0		0		0		0		ns

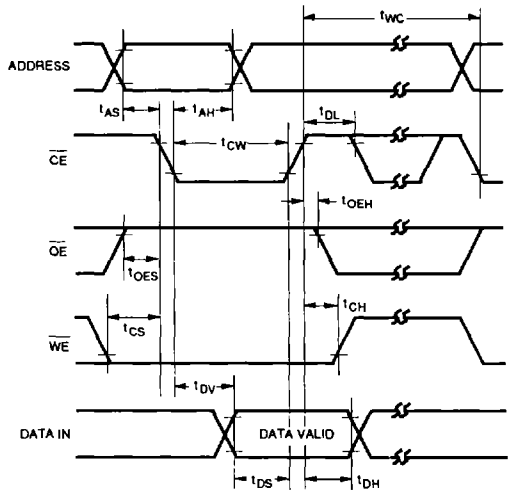
NOTES:
1. $\overline{WE}$ is noise protected. Less than a 20 ns write pulse will not activate a write cycle.
2. Data must be valid within 1 µs maximum after the initiation of a write cycle.

TTL Byte Write Cycle

$\overline{WE}$ CONTROLLED WRITE CYCLE



$\overline{CE}$ CONTROLLED WRITE CYCLE



Ordering Information

D Q 5516A – 200
D Q 2816A H – 200

PACKAGE TYPE	TEMPERATURE RANGE	PART TYPE	EEPROM BYTE WRITE TIME	ACCESS TIME
D – CERAMIC DIP P – PLASTIC DIP UX – UNENCAPSULATED DIE	Q – 0°C TO + 70°C (COMMERCIAL)	2K x 8 EEPROM	(BLANK) – STANDARD WRITE TIME H – FAST WRITE TIME	200 = 200 ns 250 = 250 ns 300 = 300 ns 350 = 350 ns